2SB0976 (2SB976)

Silicon PNP epitaxial planar type

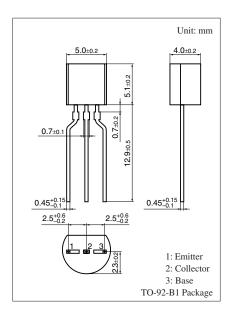
For low-frequency output amplification For DC-DC converter For stroboscope

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- Large collector current I_C

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-27	V	
Collector-emitter voltage (Base open)	V _{CEO}	-18	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_C	-5	A	
Peak collector current	I_{CP}	-8	A	
Collector power dissipation	P_{C}	0.75	W	
Junction temperature	T_j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

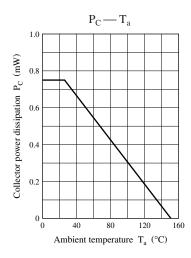
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-18			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \ \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$			-1	μΑ
Forward current transfer ratio *1, 2	h _{FE}	$V_{CE} = -2 \text{ V}, I_{C} = -2 \text{ A}$	125		625	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -3 \text{ A}, I_B = -0.1 \text{ A}$		- 0.4	-1.0	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		60		pF
(Common base, input open circuited)						

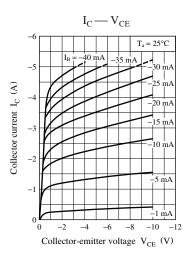
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

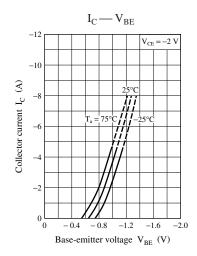
- 2. *1: Pulse measurement
 - *2: Rank classification

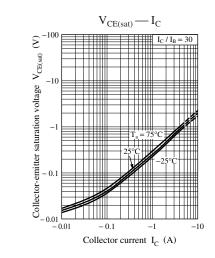
Rank	Q	R
h_{FE}	125 to 205	180 to 625

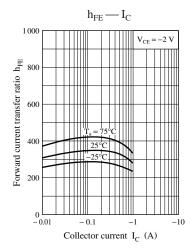
Note) The part number in the parenthesis shows conventional part number.

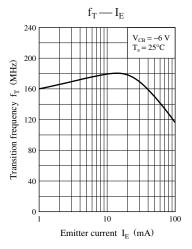


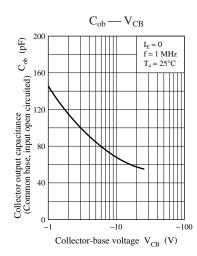












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